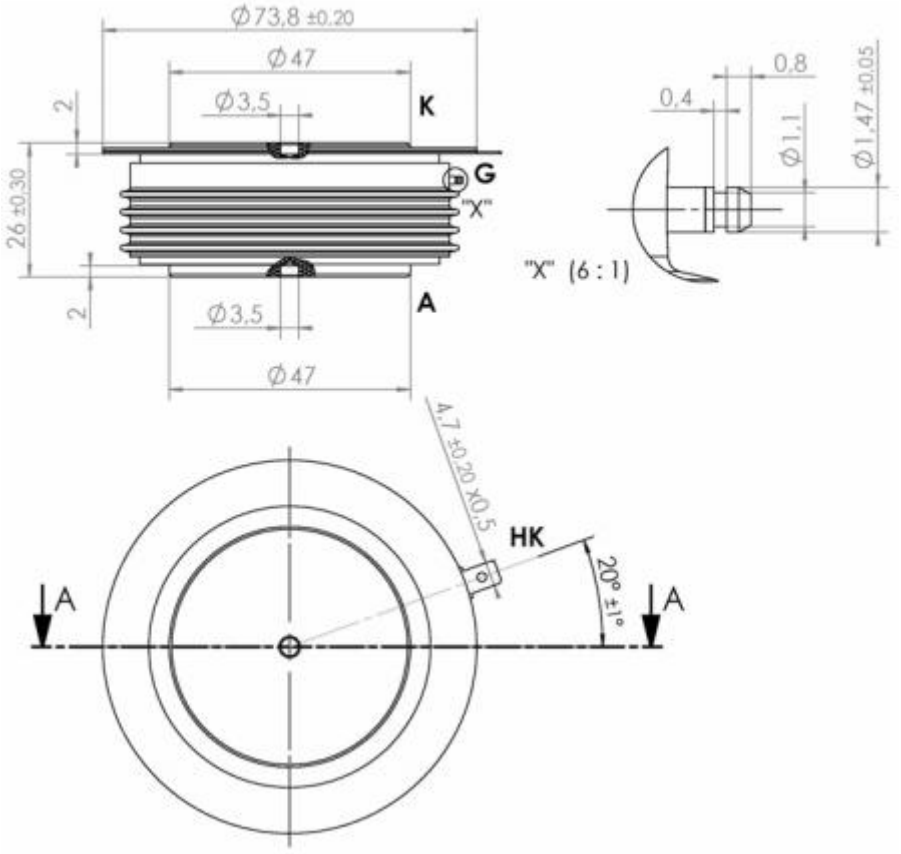
Absolute Maximum Ratings				
Symbol	**Conditions**		**Values**	**Unit**
Chip				
$I_{T(AV)}$	sinus 180°	T_c = 85 °C	1200	A
		T_c = 100 °C	840	A
I_{TSM}	10 ms	T_j = 25 °C	30000	A
		T_j = 125 °C	25500	A
i^2t	10 ms	T_j = 25 °C	4500000	A^2s
		T_j = 125 °C	3251250	A^2s
V_{RSM}			1200	V
V_{RRM}			1200	V
V_{DRM}			1200	V
$(di/dt)_{cr}$	T_j = 125 °C		125	A/µs
$(dv/dt)_{cr}$	T_j = 125 °C		1000	V/µs
T_j			-40 ... +125	°C
Module				
T_{stg}			-40 ... +130	°C

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
Chip						
V_T	T_j = 25 °C, I_T = 3600 A				1.65	V
$V_{T(TO)}$	T_j = 125 °C				0.95	V
r_T	T_j = 125 °C				0.18	mΩ
$I_{DD};I_{RD}$	T_j = 125 °C, $V_{DD} = V_{DRM}$; $V_{RD} = V_{RRM}$				160	mA
t_{gd}	T_j = 25 °C, I_G = 1 A, di_G/dt = 1 A/µs			1		µs
t_{gr}	$V_D = 0.67 * V_{DRM}$			2		µs
t_q	T_j = 125 °C		100		250	µs
I_H	T_j = 25 °C			250	500	mA
I_L	T_j = 25 °C, R_G = 33 Ω			500	2000	mA
V_{GT}	T_j = 25 °C, d.c.		3			V
I_{GT}	T_j = 25 °C, d.c.		250			mA
V_{GD}	T_j = 125 °C, d.c.				0.25	V
I_{GD}	T_j = 125 °C, d.c.				10	mA
$R_{th(j-c)}$	continuous DC	SSC				K/W
		DSC			0.021	K/W
$R_{th(j-c)}$	sin. 180°	SSC			0.054	K/W
		DSC			0.0225	K/W
$R_{th(j-c)}$	rec. 120°	SSC			0.06	K/W
		DSC			0.027	K/W
Module						
$R_{th(c-s)}$	SSC			0.01		K/W
	DSC			0.005		K/W
F			22		25	KN
a						m/s^2
w				480		g


Ø73,8 ±0.20
Ø47
Ø3,5
K
2
26 ±0.30
G
"X"
2
Ø3,5
A
Ø47
0,8
0,4
Ø1,1
Ø1,47 ±0.05
"X" (6 : 1)
4,7 ±0.20 x0,5
HK
20° ±1°
A
A